# **PBSS4240X**

# 40 V, 2 A NPN low VCEsat (BISS) transistor

**15 October 2012** 

**Product data sheet** 

# 1. Product profile

#### 1.1 General description

NPN low  $V_{CEsat}$  Breakthrough In Small Signal (BISS) transistor in a medium power and flat lead SOT89 Surface-Mounted Device (SMD) plastic package. PNP complement: PBSS5240X.

#### 1.2 Features and benefits

- Low collector-emitter saturation voltage V<sub>CEsat</sub>
- High collector current capability I<sub>C</sub> and I<sub>CM</sub>
- · High efficiency due to less heat generation

### 1.3 Applications

- DC-to-DC conversion
- Supply line switching
- Battery charger
- LCD backlighting
- Driver in low supply voltage applications (e.g. lamps and LEDs)
- Inductive load driver (e.g. relays, buzzers and motors)

### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>CEO</sub>	collector-emitter voltage	open base	-	-	40	V
I <sub>C</sub>	collector current		-	-	2	Α
I <sub>CM</sub>	peak collector current		-	-	3	Α
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_C$ = 1 A; $I_B$ = 100 mA; pulsed; $t_p \le 300$ μs; δ ≤ 0.02 ; $T_{amb}$ = 25 °C	-	-	260	mΩ
I <sub>CRM</sub>	repetitive peak collector current	$t_p \le 20 \text{ ms};  \delta \le 0.33 \; ;  \text{pulsed}$	-	-	2.5	Α



40 V, 2 A NPN low VCEsat (BISS) transistor

# 2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	Е	emitter		C
2	С	collector		В
3	В	base	3 2 1	- <b>N</b>
			SOT89	sym123

# 3. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PBSS4240X	SOT89	plastic surface-mounted package; die pad for good heat transfer; 3 leads	SOT89		

# 4. Marking

Table 4. Marking codes

Type number	Marking code
PBSS4240X	S47

# 5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>CBO</sub>	collector-base voltage	open emitter		-	40	V
V <sub>CEO</sub>	collector-emitter voltage	open base		-	40	V
V <sub>EBO</sub>	emitter-base voltage	open collector		-	5	V
I <sub>C</sub>	collector current			-	2	Α
I <sub>CRM</sub>	repetitive peak collector current	$\delta \le 0.33$ ; $t_p \le 20$ ms; pulsed		-	2.5	Α
I <sub>CM</sub>	peak collector current			-	3	Α
I <sub>B</sub>	base current			-	300	mA
I <sub>BM</sub>	peak base current			-	1	Α
P <sub>tot</sub>	total power dissipation		[1]	-	0.5	W
			[2]	-	0.95	W

PBSS4240X

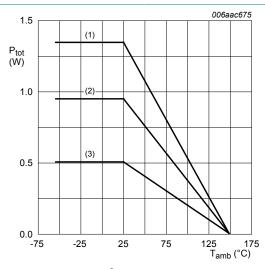
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Symbol	Parameter	Conditions		Min	Max	Unit
			[3]	-	1.35	W
T <sub>j</sub>	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-65	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.



- (1) FR4 PCB, mounting pad for collector 6 cm<sup>2</sup>
- (2) FR4 PCB, mounting pad for collector 1 cm<sup>2</sup>
- (3) FR4 PCB, standard footprint

Fig. 1. Power derating curves

### 6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance	in free air	[1]	-	-	250	K/W
from junction to ambient	-		[2]	-	-	132	K/W
	ambient		[3]	-	-	93	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	-	16	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.

PBSS4240X

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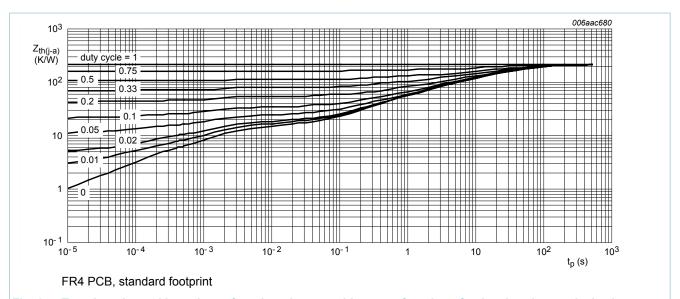


Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

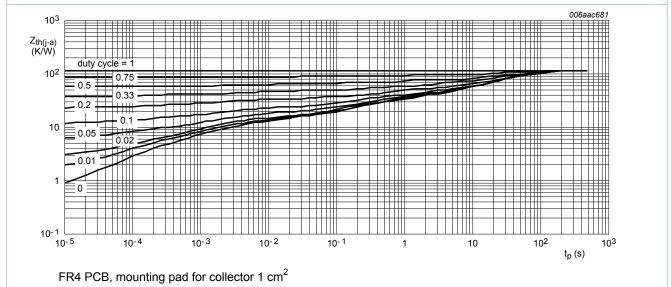
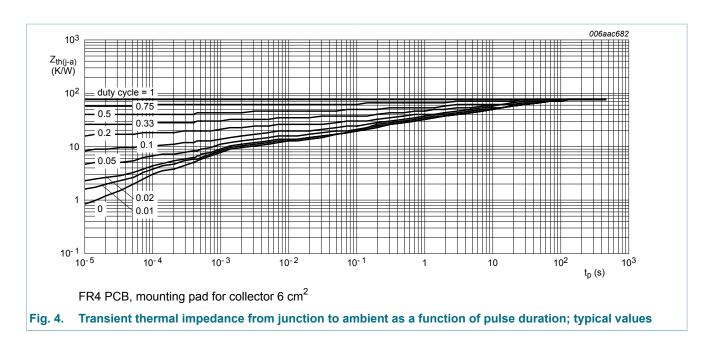


Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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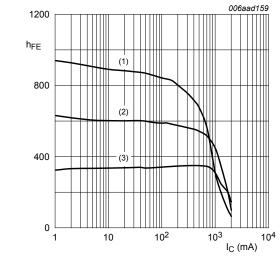
# 7. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>CBO</sub>	collector-base cut-off	V <sub>CB</sub> = 40 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	100	nA
	current	V <sub>CB</sub> = 40 V; I <sub>E</sub> = 0 A; T <sub>j</sub> = 150 °C	-	-	50	μA
I <sub>CEO</sub>	collector-emitter cut-off current	V <sub>CE</sub> = 30 V; I <sub>B</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	100	nA
I <sub>EBO</sub>	emitter-base cut-off current	V <sub>EB</sub> = 5 V; I <sub>C</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	100	nA
h <sub>FE</sub>	DC current gain	V <sub>CE</sub> = 5 V; I <sub>C</sub> = 1 mA; T <sub>amb</sub> = 25 °C	300	-	-	
		V <sub>CE</sub> = 5 V; I <sub>C</sub> = 500 mA; T <sub>amb</sub> = 25 °C	300	-	900	
		V <sub>CE</sub> = 5 V; I <sub>C</sub> = 1 A; T <sub>amb</sub> = 25 °C	200	-	-	
		$V_{CE}$ = 5 V; $I_{C}$ = 2 A; pulsed; $t_{p}$ ≤ 300 μs; $\delta$ ≤ 0.02 ; $T_{amb}$ = 25 °C	75	-	-	
V <sub>CEsat</sub>	collector-emitter	I <sub>C</sub> = 100 mA; I <sub>B</sub> = 1 mA; T <sub>amb</sub> = 25 °C	-	-	80	mV
	saturation voltage	I <sub>C</sub> = 500 mA; I <sub>B</sub> = 50 mA; T <sub>amb</sub> = 25 °C	-	-	140	mV
		$I_C$ = 1 A; $I_B$ = 100 mA; pulsed; $t_p \le 300 \ \mu s$ ; $\delta \le 0.02$ ; $T_{amb}$ = 25 °C	-	-	260	mV
		$I_{C}$ = 2 A; $I_{B}$ = 200 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 \ ; T_{amb}$ = 25 °C	-	-	510	mV
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_C$ = 1 A; $I_B$ = 100 mA; pulsed; $t_p \le 300 \ \mu s$ ; $\delta \le 0.02$ ; $T_{amb}$ = 25 °C	-	-	260	mΩ

### 40 V, 2 A NPN low VCEsat (BISS) transistor

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>BEsat</sub>	base-emitter saturation voltage	$I_C$ = 1 A; $I_B$ = 100 mA; pulsed; $t_p \le 300$ μs; $\delta \le 0.02$ ; $T_{amb}$ = 25 °C	-	-	1.2	V
V <sub>BEon</sub>	base-emitter turn-on voltage	$V_{CE}$ = 5 V; $I_{C}$ = 1 A; pulsed; $t_{p}$ ≤ 300 $\mu$ s; $\delta$ ≤ 0.02 ; $T_{amb}$ = 25 °C	-	-	1.1	V
f <sub>T</sub>	transition frequency	$V_{CE}$ = 10 V; $I_{C}$ = 50 mA; f = 100 MHz; $T_{amb}$ = 25 °C	150	-	-	MHz
C <sub>c</sub>	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = 0 \text{ A}; i_e = 0 \text{ A};$ $f = 1 \text{ MHz}; T_{amb} = 25 ^{\circ}\text{C}$	-	-	10	pF



 $V_{CE} = 5 V$ 

(1)  $T_{amb}$  = 150 °C

(2)  $T_{amb}$  = 25 °C

(3)  $T_{amb} = -55 \, ^{\circ}C$ 

Fig. 5. DC current gain as a function of collector current; typical values

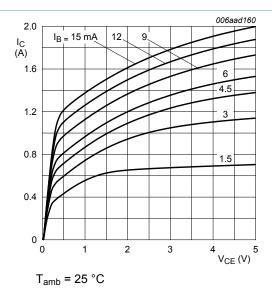
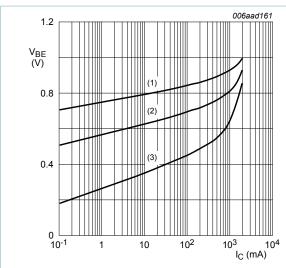


Fig. 6. Collector current as a function of collectoremitter voltage; typical values

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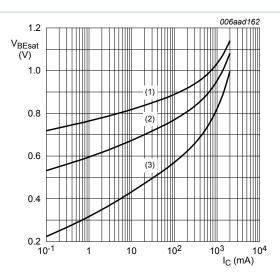
$$V_{CE} = 5 V$$

(1) 
$$T_{amb} = -55 \,^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = 150 \, ^{\circ}C$$

Fig. 7. Base-emitter voltage as a function of collector current; typical values



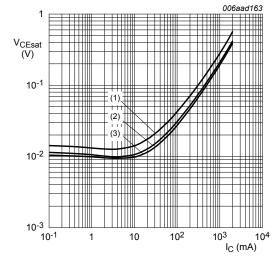
$$I_{\rm C}/I_{\rm B} = 20$$

(1) 
$$T_{amb} = -55 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = 150 \, ^{\circ}C$$

Fig. 8. Base-emitter saturation voltage as a function of collector current; typical values

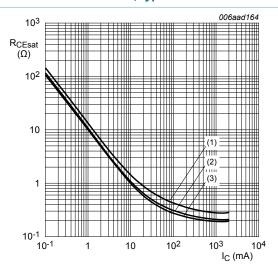


$$I_{\rm C}/I_{\rm B} = 20$$

(1) 
$$T_{amb} = 150 \, ^{\circ}C$$

(3) 
$$T_{amb}$$
= -55 °C

Fig. 9. Collector-emitter saturation voltage as a function of collector current; typical values



$$I_{\rm C}/I_{\rm B} = 20$$

(1) 
$$T_{amb} = 150 \, ^{\circ}C$$

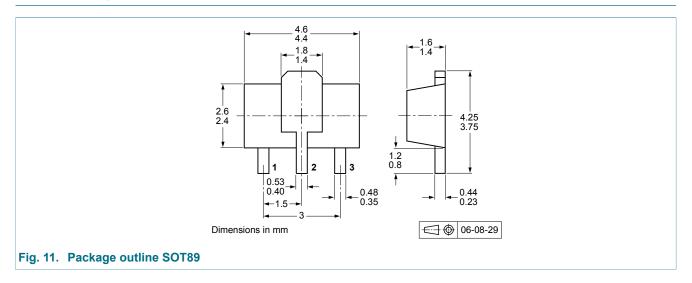
(2) 
$$T_{amb}$$
 = 25 °C

$$(3) T_{amb} = -55 °C$$

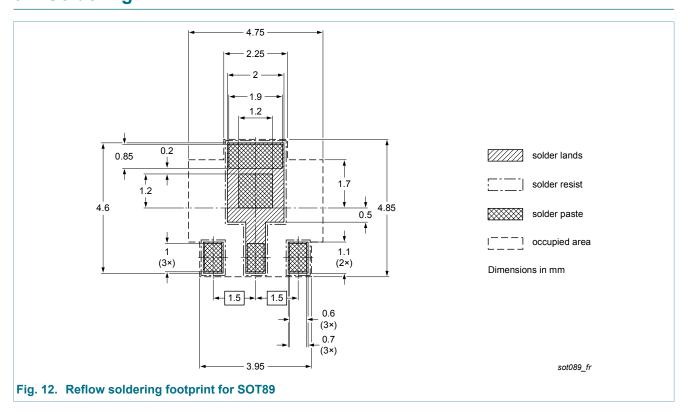
Fig. 10. Collector-emitter saturation resistance as a function of collector current; typical values

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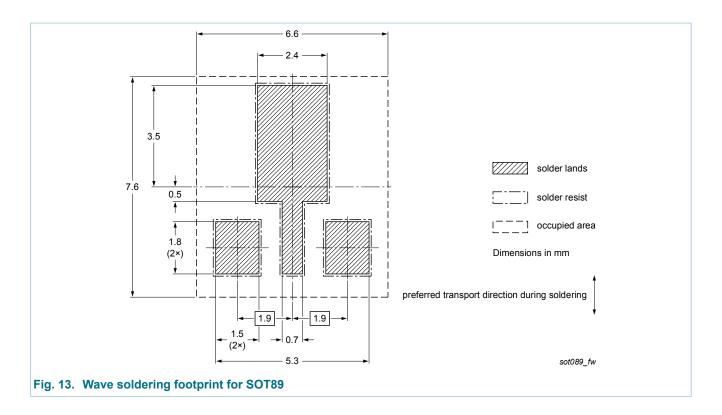
# 8. Package outline



# 9. Soldering



### 40 V, 2 A NPN low VCEsat (BISS) transistor



# 10. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PBSS4240X v.1	20121015	Product data sheet	-	-

#### 40 V, 2 A NPN low VCEsat (BISS) transistor

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### 40 V, 2 A NPN low VCEsat (BISS) transistor

# 12. Contents

1	Product profile	1
1.1	General description	
1.2	Features and benefits	1
1.3	Applications	1
1.4	Quick reference data	1
2	Pinning information	2
3	Ordering information	2
4	Marking	2
5	Limiting values	2
6	Thermal characteristics	3
7	Characteristics	5
8	Package outline	8
9	Soldering	8
10	Revision history	9
11	Legal information	10
11.1	Data sheet status	10
11.2	Definitions	10
11.3	Disclaimers	10
11.4	Trademarks	11

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12/12